Fast Silicon Mesa Rectifiers

Features

- Glass passivated junction
- Hermetically sealed package
- Low reverse current
- Soft recovery characteristics

94 9539

Applications

Fast "soft recovery" rectifier

Absolute Maximum Ratings

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Туре	Symbol	Value	Unit
Reverse voltage		BYV37	V _R	800	V
		BYV38	V _R	1000	V
Peak forward surge current	t _p =10ms		I _{FSM}	50	А
Average forward current			I _{FAV}	2	А
Junction temperature			Tj	175	°C
Storage temperature range			T _{stg}	-65+175	°C

Maximum Thermal Resistance

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	l=10mm, T _L =constant	R _{thJA}	45	K/W
	on PC board with spacing 25 mm	R _{thJA}	100	K/W

Characteristics

$T_i = 25^{\circ}C$

Parameter	Test Conditions	Туре	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =1A		V _F		1.0	1.1	V
Reverse current	V _R		I _R		1	5	μΑ
	$V_R, T_j=150^{\circ}C$		I _R		60	150	μΑ
Reverse recovery time	$I_{F}=0.5A, I_{R}=1A, i_{R}=0.25A$		t _{rr}			300	ns

Typical Characteristics ($T_j = 25^{\circ}C$ unless otherwise specified)

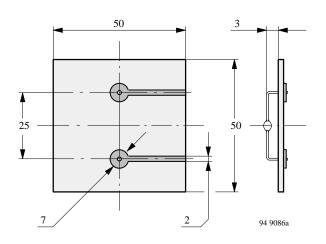


Figure 1 : Epoxy glass hard tissue, board thickness 1.5 mm, $R_{thJA} \! \leq \! 100 \; \text{K/W}$

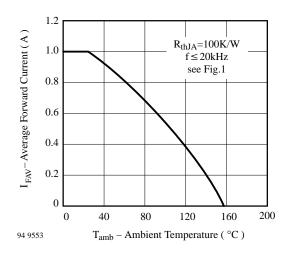


Figure 3 : Average Forward Current vs. Ambient Temperature

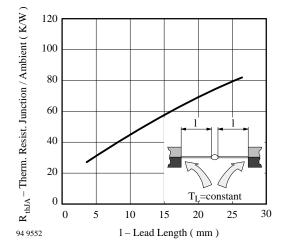


Figure 2 : Thermal Resistance vs. Lead Length

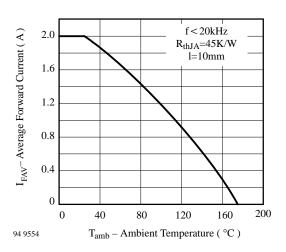


Figure 4 : Average Forward Current vs. Ambient Temperature

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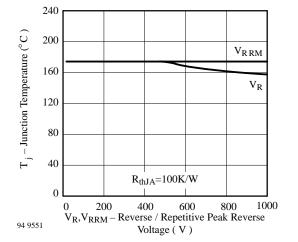


Figure 5 : Junction Temperature vs. Reverse/Repetitive Peak Reverse Voltage

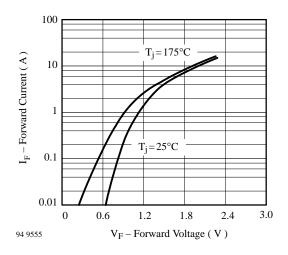
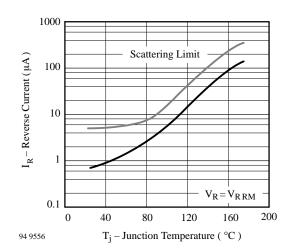


Figure 7 : Forward Current vs. Forward Voltage



BYV37.BYV38

Figure 6 : Reverse Current vs. Junction Temperature

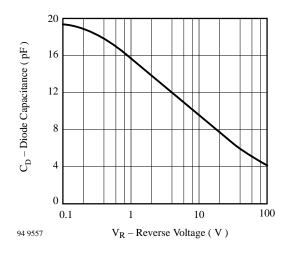


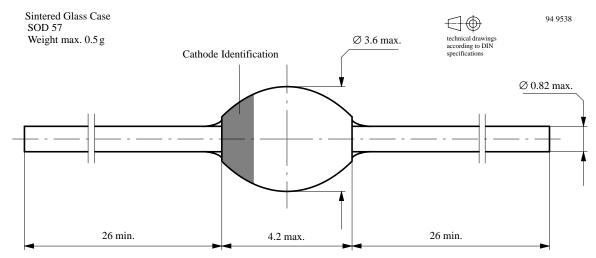
Figure 8 : Diode Capacitance vs. Reverse Voltage

BYV37.BYV38

Τεμις

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Dimensions in mm



OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements and
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

Of particular concern is the control or elimination of releases into the atmosphere of those substances which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) will soon severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of any ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA and
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with and do not contain ozone depleting substances.

We reserve the right to make changes to improve technical design without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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